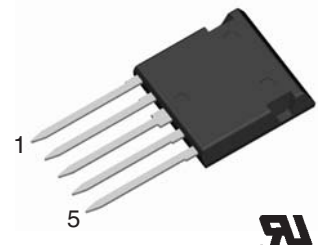
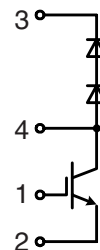


Fast IGBT Chopper

in ISOPLUS i4-PAC™

$I_{C25} = 38 \text{ A}$
 $V_{CES} = 600 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 1.9 \text{ V}$

Preliminary data



IGBT			
Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	38	A
I_{C90}	$T_C = 90^{\circ}\text{C}$	24	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 10 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	110	A
		V_{CES}	
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 10 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	125	W

Features

- NPT IGBT technology
 - low switching losses for high frequency operation
 - no latch up
 - positive temperature coefficient for easy paralleling
- HiPerDyn™ FRED
 - consisting of series connected diodes
 - enhanced dynamic behaviour for high frequency operation
- ISOPLUS i4-PAC™ package
 - isolated back surface
 - low coupling capacity between pins and heatsink
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - industry standard outline
 - UL registered E 72873

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 25 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.9 2.2	2.4	V V
$V_{GE(th)}$	$I_C = 0.7 \text{ mA}; V_{GE} = V_{CE}$	3	5	V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1	0.04	mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$		200	nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 25 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 10 \Omega$	30		ns
		50		ns
		320		ns
		70		ns
		1.1		mJ
		0.6		mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$	1.6		nF
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 15 \text{ A}$	140		nC
R_{thJC} R_{thJH}	(with heat transfer paste)	2.0	1.0	K/W K/W

Applications

- boost chopper for power factor correction
- supply of high frequency transformer
 - switched mode power supplies
 - welding converters

IXYS reserves the right to change limits, test conditions and dimensions.

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Diodes (data for series connection)

Symbol	Conditions	Maximum Ratings	
V_{RRM}	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C	600	V
I_{F25}	$T_C = 25^{\circ}\text{C}$	35	A
I_{F90}	$T_C = 90^{\circ}\text{C}$	20	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 25\text{ A}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.8	3.7	V
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.1	0.1	mA
I_{RM} t_{rr}	} $I_F = 15\text{ A}$; $di_F/dt = -400\text{ A}/\mu\text{s}$; $T_{VJ} = 125^{\circ}\text{C}$ $V_R = 300\text{ V}$; $V_{GE} = 0\text{ V}$	8		A
		50		ns
R_{thJC} R_{thJH}	(per diode)	2.3		1.2 K/W K/W

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	$^{\circ}\text{C}$
T_{stg}		-55...+125	$^{\circ}\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case		40	pF
d_S, d_A	pin - pin	1.7		mm
d_S, d_A	pin - backside metal	5.5		mm
Weight		9		g

Dimensions in mm (1 mm = 0.0394")
